

## **Integrated circuit capacitor in multi-level metallization**

### **ABSTRACT**

An integrated circuit capacitor is formed by first  
5 forming a first dielectric layer (25) over a semiconductor  
(10). A copper structure (35) is formed in the first  
dielectric layer (25) and a second dielectric layer (80) is  
formed over the copper structure (35). A metal containing  
layer (90) is formed over the second dielectric layer (80)  
10 and the copper structure (35) and a planar surface is  
formed by removing portions of the metal containing layer  
(90) and the second dielectric layer (80).